



Half-bridge SCR configuration integrated
in a single package
High-thermal-conductivity DBC insulation for excellent
heat dissipation
Vacuum soldering technology for enhanced reliability

Heating control
Light control system
DC motor

(@ $T_C = 25^{\circ}\text{C}$ unless otherwise specified)

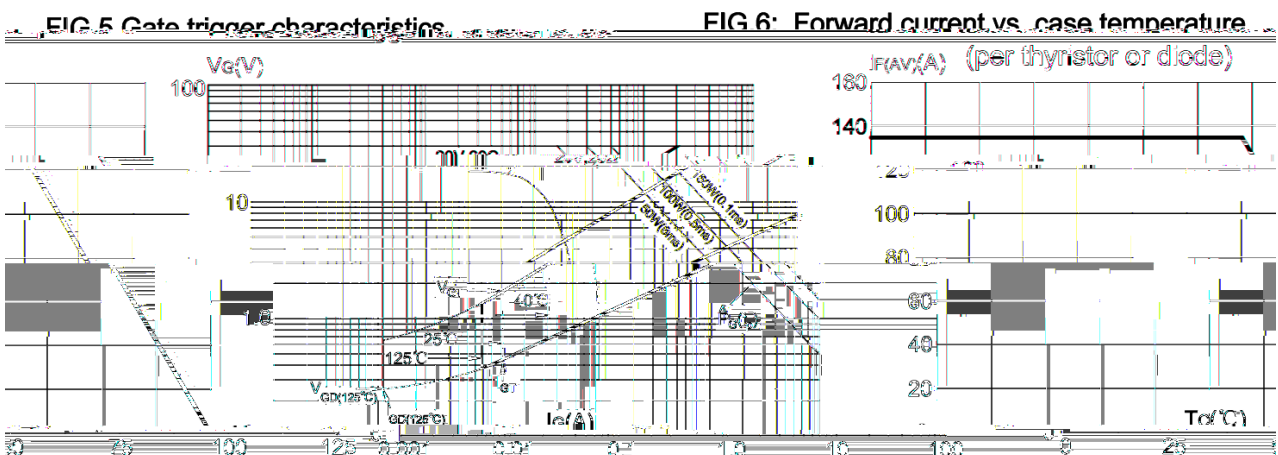
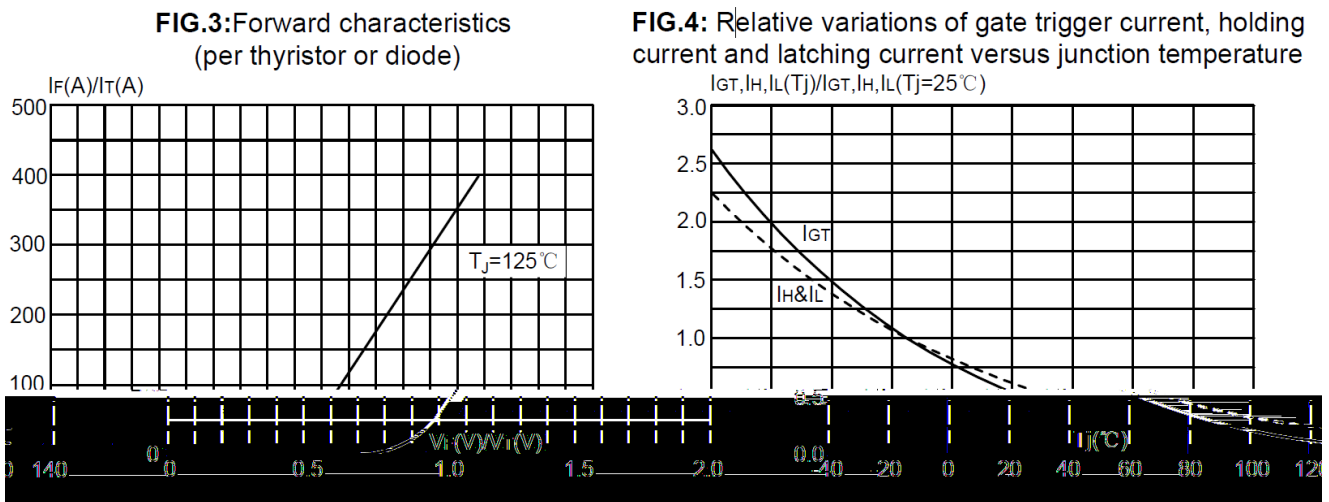
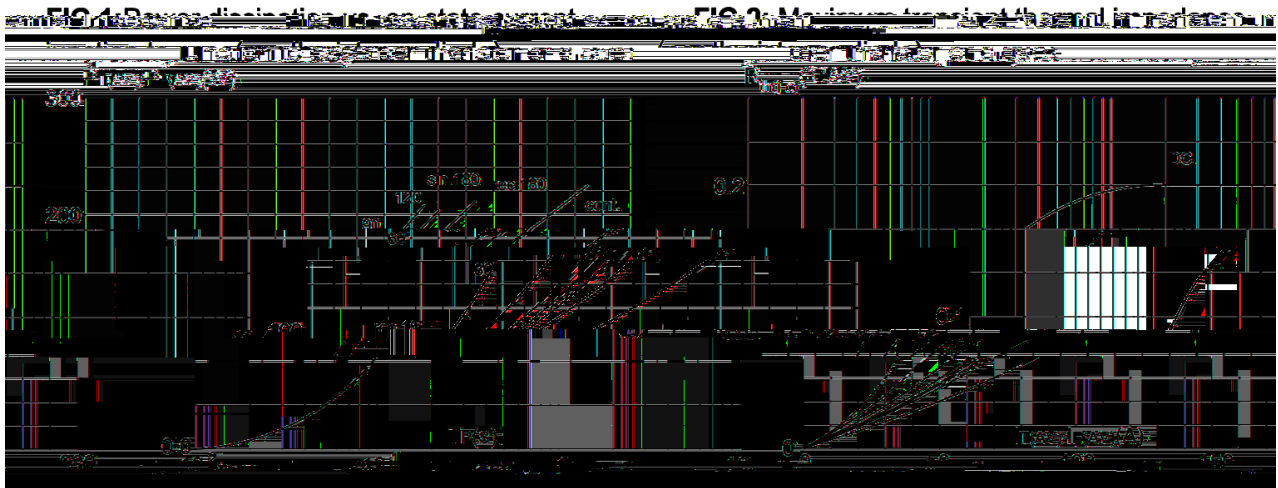
Repetitive peak off-state voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{DRM}	1600	V
Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1600	V
Non-repetitive peak off-state voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{DSM}	1700	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RSM}	1700	V
Average forward current	$T_C = 85^{\circ}\text{C}$	$I_{\text{T(AV)}}$	136	A

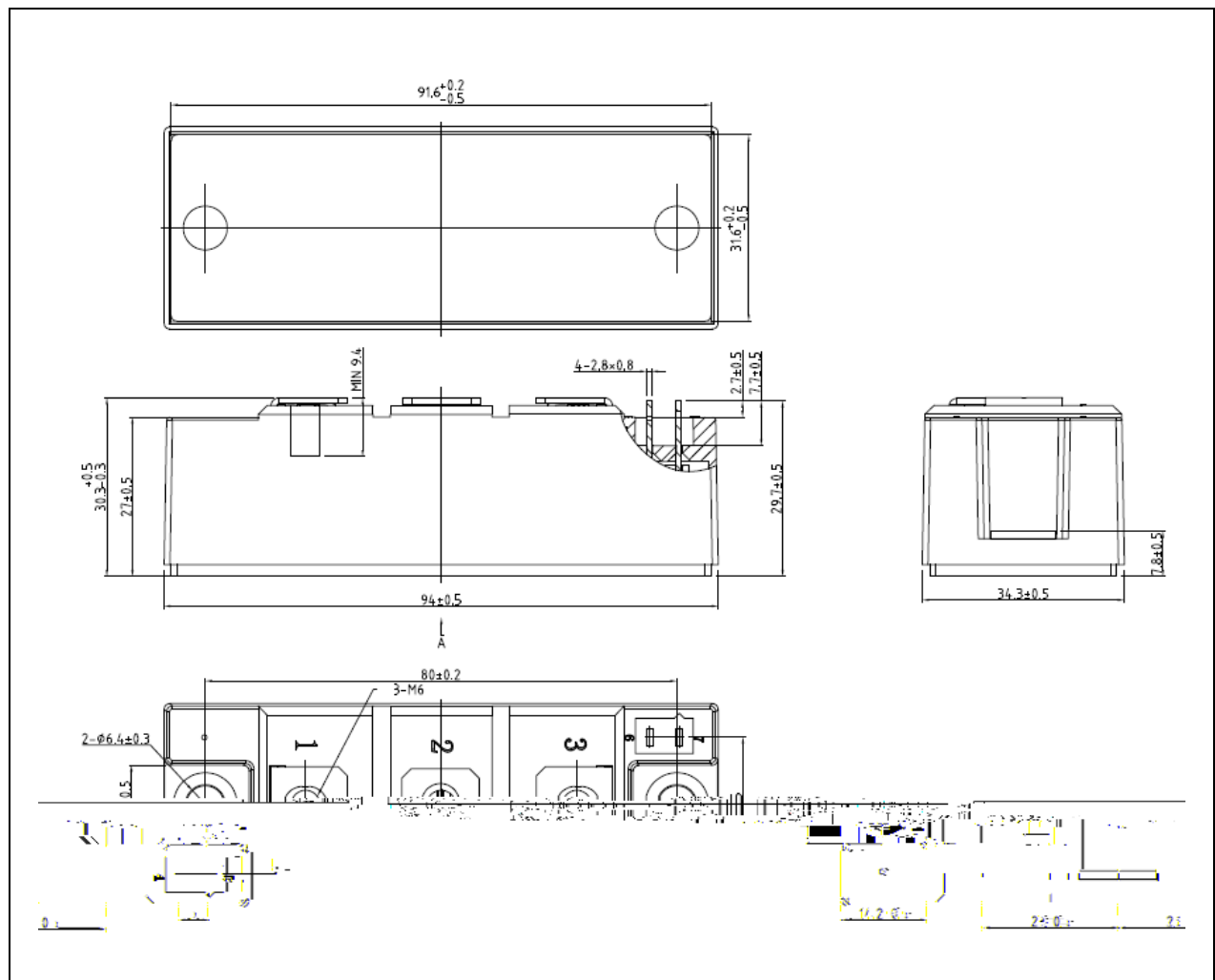
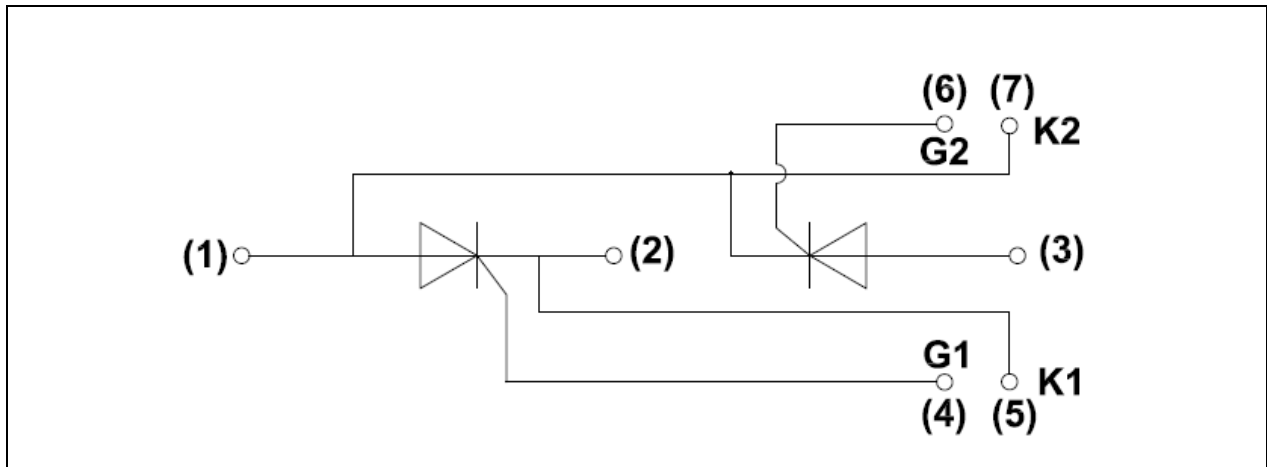


(@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Peak forward voltage	$I_T=410\text{A}$, $t_p=380$	V_T			1.80	V
Repetitive peak off-state current	$V_D = V_{\text{DRM}}$, $T_{vj} = 25^\circ\text{C}$	I_{DRM}			100	A
	$V_D = V_{\text{DRM}}$, $T_{vj} = 125^\circ\text{C}$				50	mA
Reverse leakage current	$V_R = V_{\text{RRM}}$, $T_{vj} = 25^\circ\text{C}$	I_{RRM}			100	A
	$V_R = V_{\text{RRM}}$, $T_{vj} = 125^\circ\text{C}$				50	mA
Threshold voltage	For power loss calculation only $T_{vj} = 125^\circ\text{C}$,	V_{TO}			0.9	V
Dynamic resistance	$T_{vj} = 125^\circ\text{C}$,	r_T			1.7	
Triggering gate current	$V_D=12\text{V}$ R_L	I_{GT}	20		120	mA
Holding current	$I_T=1\text{A}$	I_H			250	mA
Latching current	$I_G=1.2 I_{\text{GT}}$	I_L			300	mA
Critical rate of rise of voltage	$V_D=2/3V_{\text{DRM}}$ $T_{vj}=125^\circ\text{C}$ Gate Open	dv/dt	1000			
Triggering gate voltage	$V_D=12\text{V}$ R_L	V_{GT}			1.8	V
Non triggering gate voltage	$V_D=0.5V_{\text{DRM}}$ $T_{vj}=125^\circ\text{C}$	V_{GD}	0			

JMT136KT16T2C	JMT136KT16T2C	T2	170±10 g/PCS	6 PCS	72 PCS







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